

AMP5057P SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB linear LDMOS design
 Designed for UHF-Band high power pulse applications
 Built-in monitoring and protection circuits
 High reliability and ruggedness



ELECTRICAL SPECIFICATIONS: 50 Ω, 25 °C

Parameter	Specification			Notes
Power Output	1000 Watt Min			Pulse
Operating Frequency Range	595 - 605 MHz Min			
Input Pulse Characteristics	Width	Duty	PRF	
	100 μS Min	1% Nom		
Power Gain	60 dB Min			
Input Return Loss	-10 dB Max			Relative to 50 Ohm
Harmonics	-30 dBc Max			At rated Pout
Non Harmonics Spurious	-60 dBc Max			
Operating Voltage	50 VDC Nom			
Current Consumption - Average	4 Amp Max			1% DC @ rated Pout
Current Consumption - Peak	40 Amp Typ			
Input Power Protection	+8 dBm Max			<10 Sec without damage
Load VSWR Protection	∞ : 1			<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +75 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions (in mm)	220 x 165 x27 mm	Excluding connectors
Weight	TBD	
RF Connectors In/Out	SMA-F / Type-N	
DC Power / Interface Connector	7-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	FWD	N/A
2	REV	N/A
3	CURRENT SENSOR	I _b @ 50mV/100mA Typ
4	TEMP SENSOR	V _T @10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
A1	VDD	50VDC
A2	GND	Ground



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OUTLINE DRAWING